

IN THE CLAIMS:

Please amend the claims as follows, substituting any amended claim(s) for the corresponding pending claim(s):

- 1 8. (amended) A portion of an integrated circuit structure comprising:
2 a dielectric layer over a substrate;
3 a conformal tungsten layer over the dielectric layer and within openings within the
4 dielectric layer; and
5 a protective barrier layer over the tungsten layer and within the openings, wherein the
6 protective barrier layer comprises a material for which removal by chemical mechanical
7 polishing is primarily mechanical.
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- 1 9. (unchanged) The portion of an integrated circuit structure as set forth in Claim 8 wherein the
2 protective barrier layer is titanium or titanium nitride.

- 1 10. (unchanged) The portion of an integrated circuit structure as set forth in Claim 8 wherein
2 portions of the tungsten layer within the openings are thicker than portions of the tungsten layer
3 over the dielectric layer.
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1 11. (unchanged) The portion of an integrated circuit structure as set forth in Claim 8 wherein
2 the protective barrier layer overlies the entire tungsten layer.

1 12. (unchanged) The portion of an integrated circuit structure as set forth in Claim 8 wherein
2 the protective barrier layer overlies portions of the tungsten layer within the openings but not
3 portions of the tungsten layer over the dielectric layer.

1 13. (unchanged) The portion of an integrated circuit structure as set forth in Claim 8 wherein
2 the tungsten layer has a thickness of between about 4500 and 8000 angstroms.

1 14. (unchanged) The portion of an integrated circuit structure as set forth in Claim 8 wherein
2 the protective barrier layer has a thickness of between about 100 and 800 angstroms.

1 15. (unchanged) The portion of an integrated circuit structure as set forth in Claim 8 wherein
2 at least one opening within the dielectric layer is sized to form a capacitive electrode from
3 tungsten within the at least one opening.

1 16. (amended) A portion of an integrated circuit structure comprising:
2 a dielectric layer having an opening therein;
Ad 3 tungsten within the opening; and
4 a portion of a protective barrier layer over a central region of the tungsten and within the
5 opening, wherein the portion of the protective barrier layer comprises a material for which
6 removal by chemical mechanical polishing is primarily mechanical.

1 17. (unchanged) The portion of an integrated circuit structure as set forth in Claim 16 wherein
2 the portion of the protective barrier layer comprises a material for which removal by chemical
3 mechanical polishing is primarily mechanical.

1 18. (unchanged) The portion of an integrated circuit structure as set forth in Claim 16 wherein
2 the portion of the protective barrier layer is titanium or titanium nitride.

1 19. (unchanged) The portion of an integrated circuit structure as set forth in Claim 16 wherein
2 the tungsten and the portion of the protective barrier layer form an upper surface which is
3 substantially planar with an upper surface of the dielectric layer.

- 1 20. (unchanged) The portion of an integrated circuit structure as set forth in Claim 16 wherein
2 the opening within the dielectric layer is sized to form a capacitive electrode from the tungsten
3 within the opening.
- ~~1 20. (unchanged) The portion of an integrated circuit structure as set forth in Claim 16 wherein
2 the opening within the dielectric layer is sized to form a capacitive electrode from the tungsten
3 within the opening.~~